



N-Channel Enhancement Mode Field Effect Transistor

Product Summary

V_{DS}	40V
I_D	155A
$R_{DS(ON)}$ (at $V_{GS}=10V$)	2.5mohm
100% EAS Tested	
100% VDS Tested	

General Description

Split gate trench MOSFET technology
Excellent package for heat dissipation
High density cell design for low $R_{DS(ON)}$
Moisture Sensitivity Level 1
Epoxy Meets UL 94 V-0 Flammability Rating
Halogen Free

Applications

Power switching application
U



YJB155G04H

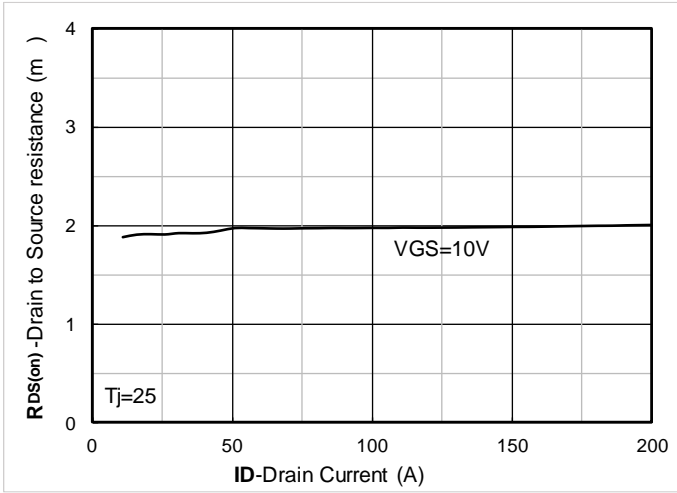


Figure7. RDS(on) VS Drain Current

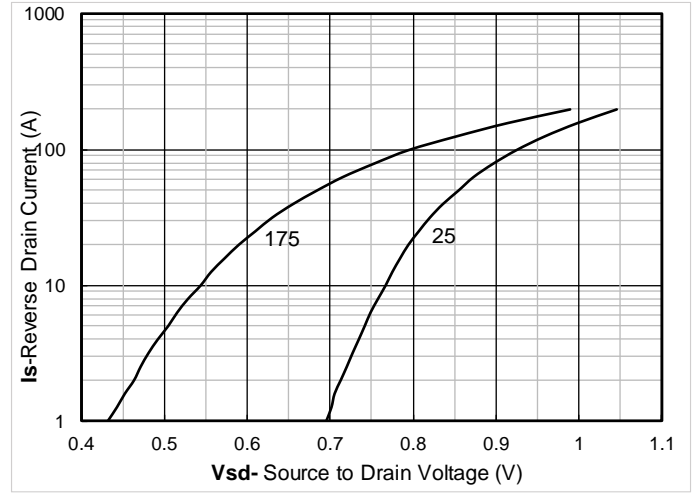


Figure8. Forward characteristics of reverse diode

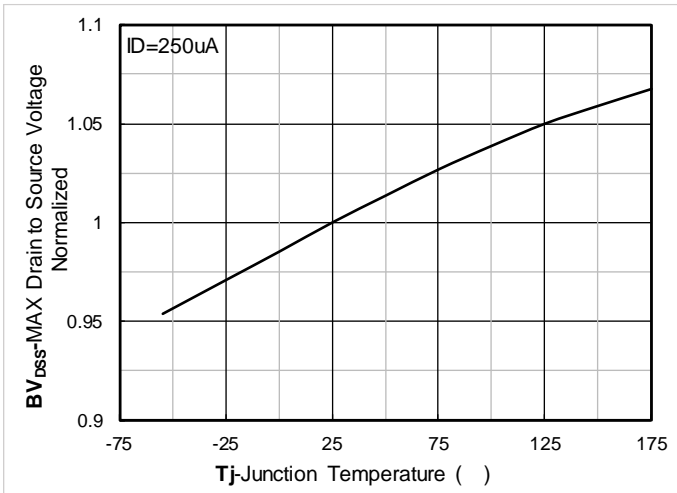


Figure9. Normalized breakdown voltage

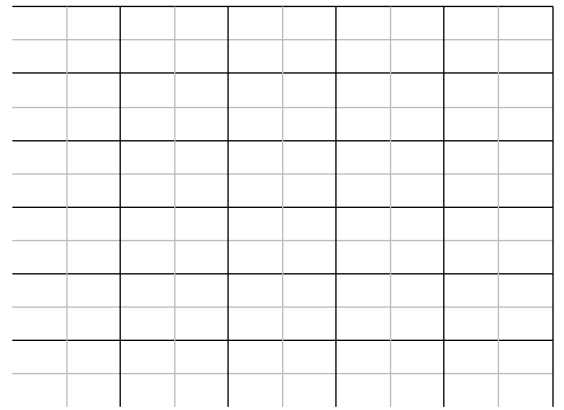


Figure10. Normalized Threshold voltage

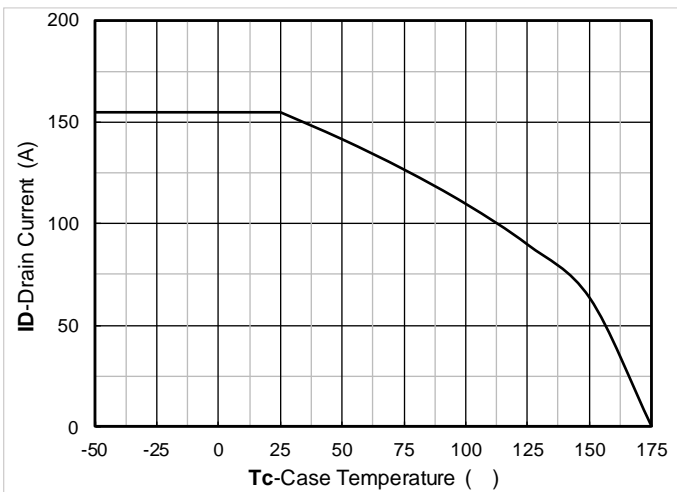


Figure11. Current dissipation

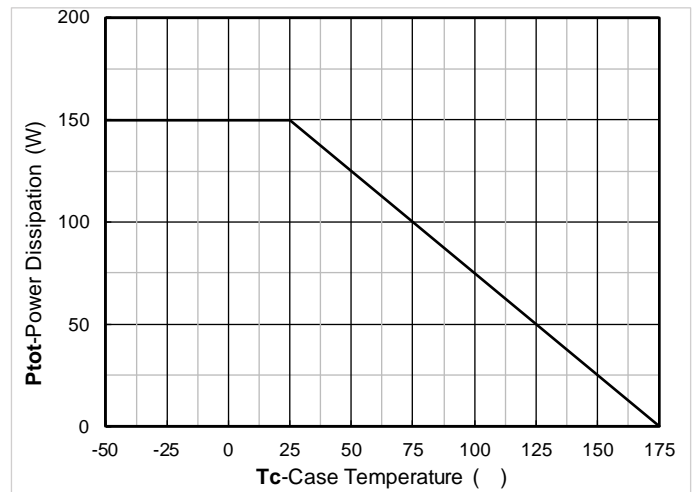


Figure12. Power dissipation



TO-263-HY Package information

SYM.	MIN.	
A2		
b2		0.050
c		
c2		
D2		
E		
E1		



Disclaimer

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